# PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

Rev. 7 — 21 December 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

NPN Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			PNP	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTC123JE	SOT416	SC-75	-	PDTA123JE	ultra small	
PDTC123JM	SOT883	SC-101	-	PDTA123JM	leadless ultra small	
PDTC123JT	SOT23	-	TO-236AB	PDTA123JT	small	
PDTC123JU	SOT323	SC-70	-	PDTA123JU	very small	

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

### 1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

#### 1.4 Quick reference data

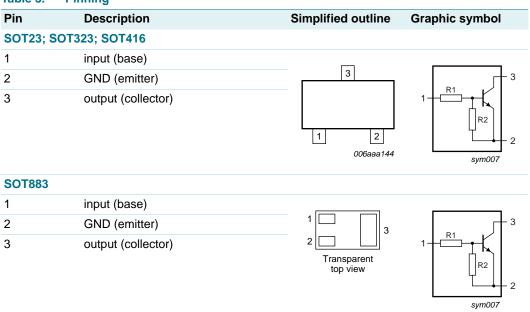
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



# 2. Pinning information

Table 3. Pinning



# 3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PDTC123JE	SC-75	plastic surface-mounted package; 3 leads	SOT416					
PDTC123JM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOT883					
PDTC123JT	-	plastic surface-mounted package; 3 leads	SOT23					
PDTC123JU	SC-70	plastic surface-mounted package; 3 leads	SOT323					

# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PDTC123JE	28
PDTC123JM	DW
PDTC123JT	*25
PDTC123JU	*49

<sup>[1] \* =</sup> placeholder for manufacturing site code.

## 5. Limiting values

Table 6. Limiting values

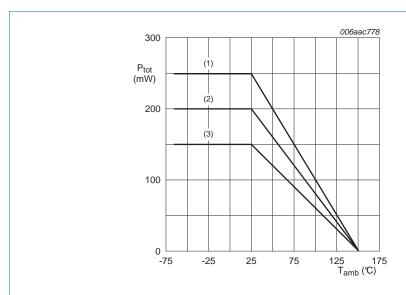
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
collector-base voltage	open emitter	-	50	V
collector-emitter voltage	open base	-	50	V
emitter-base voltage	open collector	-	10	V
input voltage				
positive		-	+12	V
negative		-	-5	V
output current		-	100	mA
peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
PDTC123JE (SOT416)		[1][2] -	150	mW
PDTC123JM (SOT883)		[2][3]	250	mW
PDTC123JT (SOT23)		<u>[1]</u> -	250	mW
PDTC123JU (SOT323)		<u>[1]</u> -	200	mW
junction temperature		-	150	°C
ambient temperature		-65	+150	°C
storage temperature		-65	+150	°C
	collector-base voltage collector-emitter voltage emitter-base voltage input voltage positive negative output current peak collector current total power dissipation PDTC123JE (SOT416) PDTC123JM (SOT883) PDTC123JU (SOT323) junction temperature ambient temperature	collector-base voltage open emitter collector-emitter voltage open base emitter-base voltage open collector input voltage positive negative output current peak collector current single pulse; $t_p \le 1$ ms total power dissipation $T_{amb} \le 25$ °C PDTC123JE (SOT416) PDTC123JM (SOT883) PDTC123JU (SOT323) junction temperature ambient temperature	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Device mounted on an FR4 PCB with 70  $\mu m$  copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70  $\mu m$  copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air				
	PDTC123JE (SOT416)		[1][2]	-	830	K/W
	PDTC123JM (SOT883)		[2][3]	-	500	K/W
	PDTC123JT (SOT23)		<u>[1]</u> -	-	500	K/W
	PDTC123JU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70  $\mu m$  copper strip line, standard footprint.

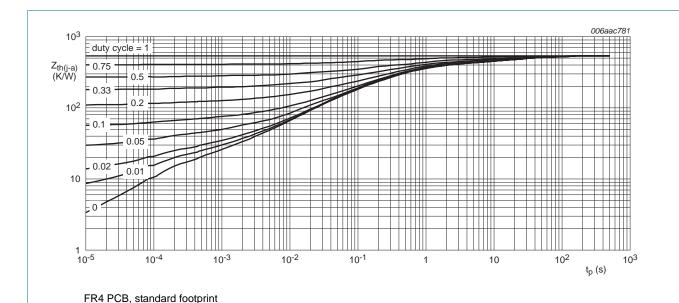
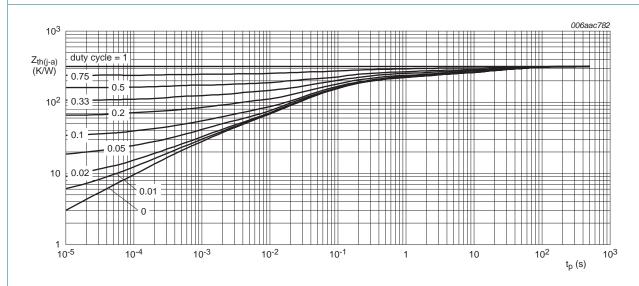
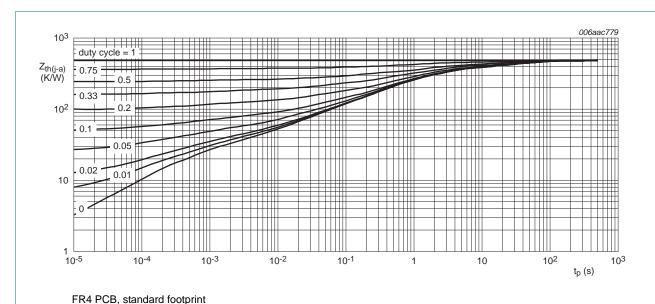


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JE (SOT416); typical values



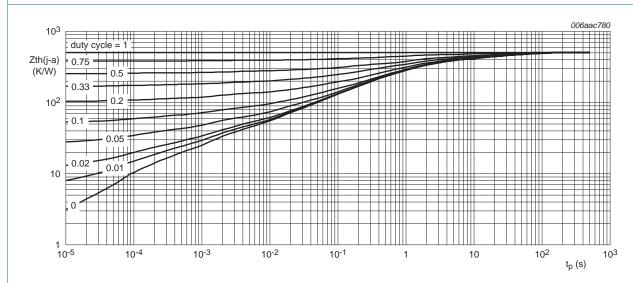
FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JM (SOT883); typical values



FR4 FCB, Standard Tootprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JT (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JU (SOT323); typical values

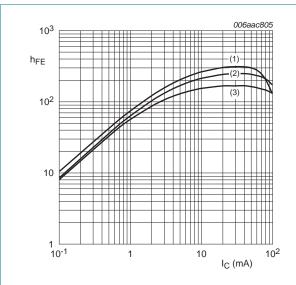
## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	1.1	0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	[1] -	230	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor.



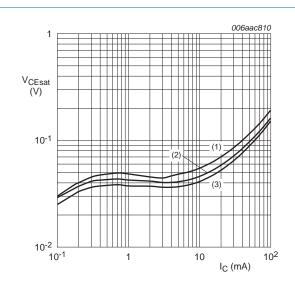
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 6. DC current gain as a function of collector current; typical values



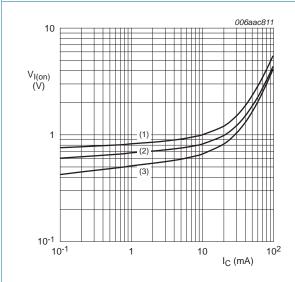
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



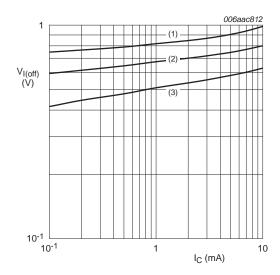
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) T<sub>amb</sub> = 100 °C

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 9. Off-state input voltage as a function of collector current; typical values

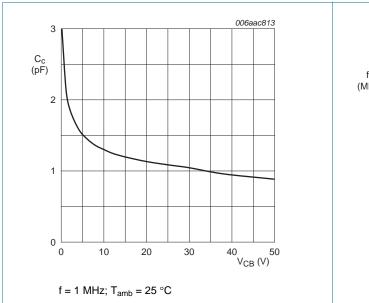


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

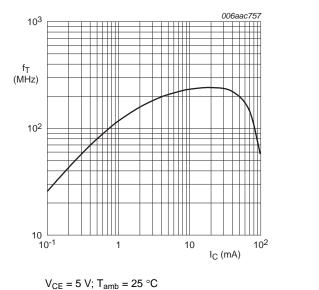


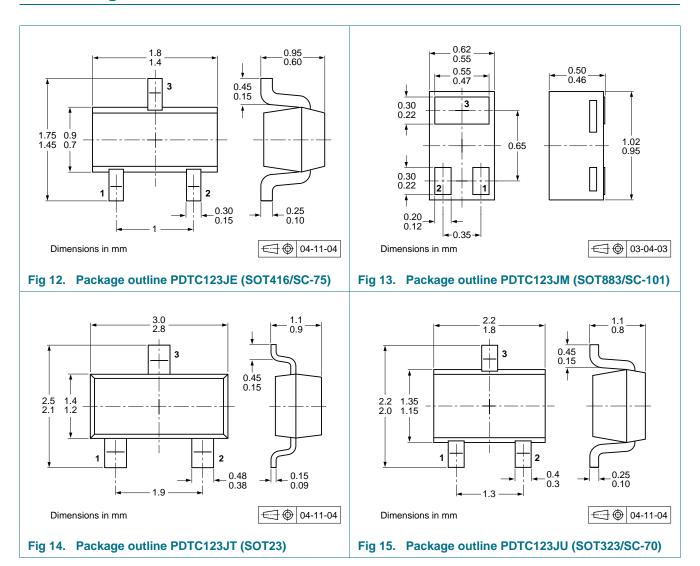
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

### 8. Test information

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing quanti		quantity
			3000	10000
PDTC123JE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135
PDTC123JM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315
PDTC123JT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PDTC123JU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

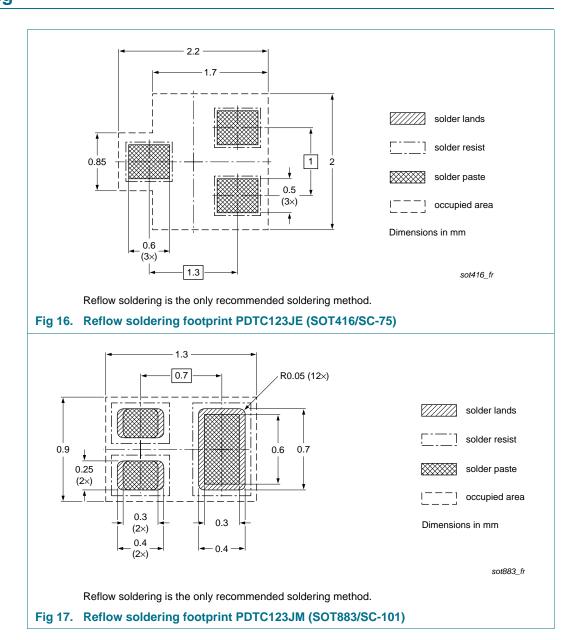
<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section 14}}$ .

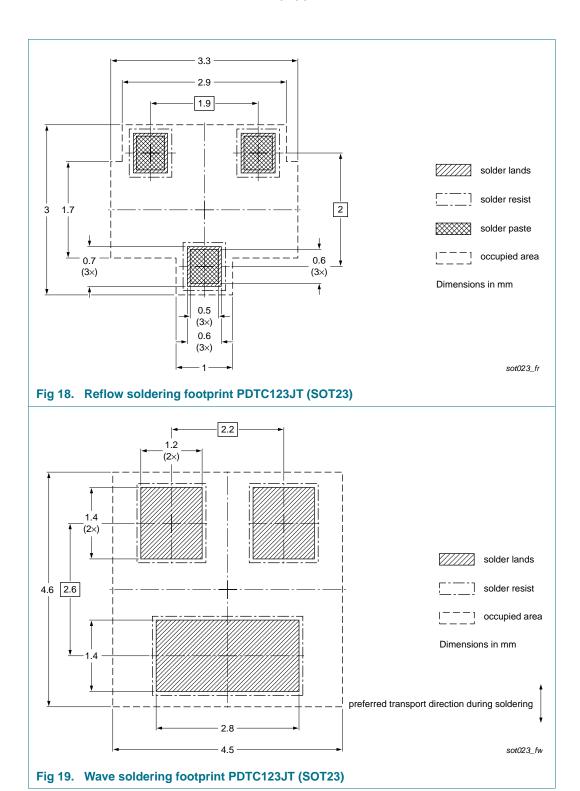
PDTC123J\_SER

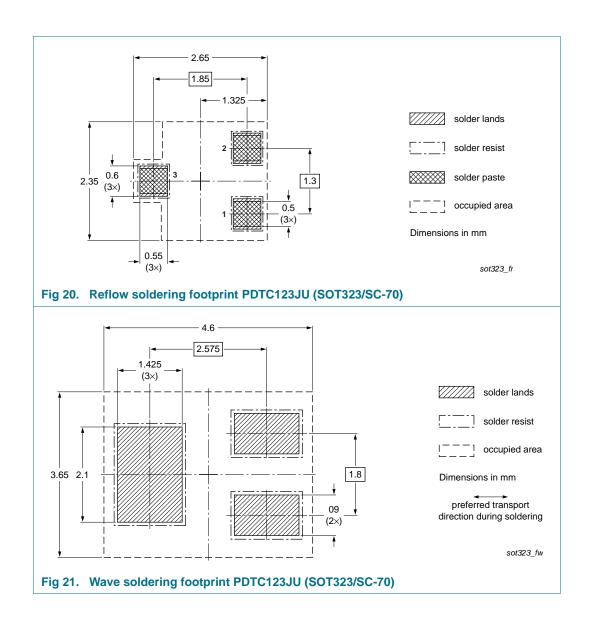
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## 11. Soldering







# 12. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC123J_SER v.7	20111221	Product data sheet	-	PDTC123J_SER v.6
Modifications:	• Figure 3 and	d <u>5</u> : corrected		
PDTC123J_SER v.6	20111215	Product data sheet	-	PDTC123J_SERIES v.5
PDTC123J_SERIES v.5	20040813	Product data sheet	-	PDTC123J_SERIES v.4
PDTC123J_SERIES v.4	20030410	Product specification	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

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# PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

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